

# BULD742C

## High voltage fast-switching NPN power transistor

### Features

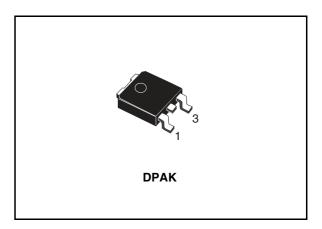
- Low spread of dynamic parameters
- High voltage capability
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

## **Applications**

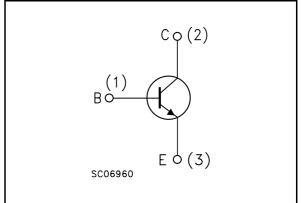
- Electronic ballast for fluorescent lighting
- Switch mode power supplies

## Description

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and high voltage capability. Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.



#### Figure 1. Internal schematic diagram



#### Table 1. Device summary

Order code	Marking	Package	Packaging
BULD742CT4	BULD742C	DPAK	Tape & reel

## Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	5
3	Test circuit	7
4	Package mechanical data	8
5	Packaging mechanical data	10
6	Revision history	11



## 1

## Electrical ratings

Symbol	Parameter	Value	Unit	
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	1050	V	
V <sub>CEO</sub>	Collector-emitter voltage ( $I_B = 0$ )	400	V	
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ , $I_B = 2$ A, $t_p < 10$ ms)	V <sub>(BR)EBO</sub>	V	
۱ <sub>C</sub>	Collector current	4	Α	
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	8	Α	
Ι <sub>Β</sub>	Base current	2	Α	
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5ms)	4	А	
P <sub>tot</sub>	Total dissipation at $T_c = 25^{\circ}C$	45	W	
T <sub>stg</sub>	Storage temperature	-65 to 150	°C	
Τ <sub>J</sub>	Max. operating junction temperature	150	°C	

#### Table 3.Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction - case	2.78	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction - ambient	73	°C/W

## 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$ 

Symbol	bol Parameter Test Conditions		Min.	Тур.	Max.	Unit
Cymson				iyp:	maxi	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> =1050 V		0.2	10	μA
I <sub>CEO</sub>	Collector cut-off current $(I_B = 0)$	V <sub>CE</sub> =400 V		10	250	μA
V <sub>(BR)EBO</sub>	Emitter base breakdown voltage ( $I_c = 0$ ) $I_E = 1 \text{ mA}$		15	19	24	V
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage $(I_B = 0)$	I <sub>C</sub> =10 mA	400	450		V
· · (1)	Collector-emitter	$I_{\rm C} = 1  {\rm A}$ $I_{\rm B} = 0.2  {\rm A}$		0.15	0.5	V
V <sub>CE(sat)</sub> <sup>(1)</sup>	saturation voltage	I <sub>C</sub> = 3.5 A I <sub>B</sub> = 1 A		0.6	1.5	V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 3.5 A I <sub>B</sub> = 1 A		1.1	1.5	V
ь (1)	DC current gain	$I_{\rm C} = 0.1  {\rm A}$ $V_{\rm CE} = 5  {\rm V}$	48	75	100	
h <sub>FE</sub> <sup>(1)</sup>		$I_{\rm C} = 0.8 \ {\rm A}$ $V_{\rm CE} = 3 \ {\rm V}$	25	35	50	
	Resistive load	$I_{\rm C} = 2 \ {\rm A}$ $V_{\rm CC} = 125 \ {\rm V}$				
t <sub>s</sub>	Storage time	I <sub>B1</sub> = -I <sub>B2</sub> = 400 mA		2.4	3.5	μs
t <sub>f</sub>	Fall time	$t_p = 300 \ \mu s$ $V_{BE(off)} = -5 \ V$		350	500	ns
_	Repetitive avalanche	L = 2 mH C = 1.8 nF				
E <sub>ar</sub>	energy	$V_{BE(off)} = -5 V$	6			mJ

#### Table 4. Electrical characteristics

1. Pulsed duration = 300 ms, duty cycle ≤ .5%



### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

#### Figure 3. Derating curve

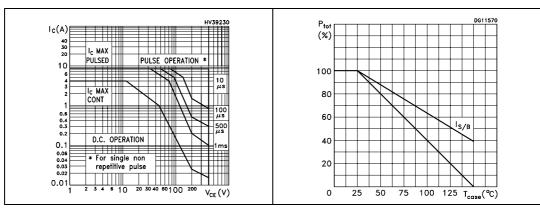


Figure 4. Output characteristics

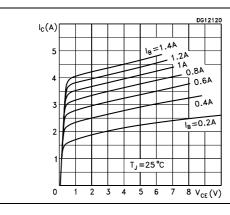


Figure 5. DC current gain

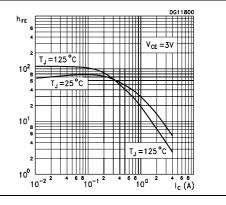
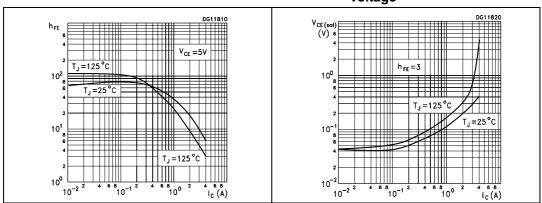
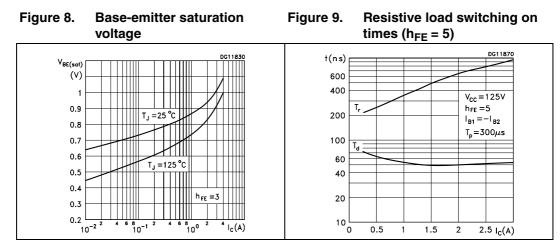


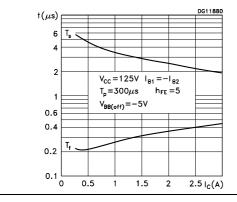
Figure 6. DC current gain

Figure 7. Collector - emitter saturation voltage









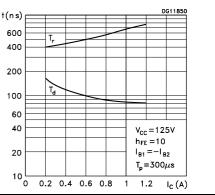
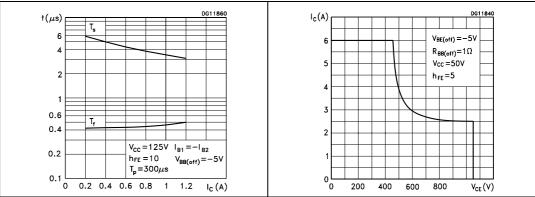
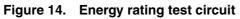


Figure 12. Resistive load switching off Figure 13. Reverse biased SOA times ( $h_{FE} = 10$ )





## 3 Test circuit



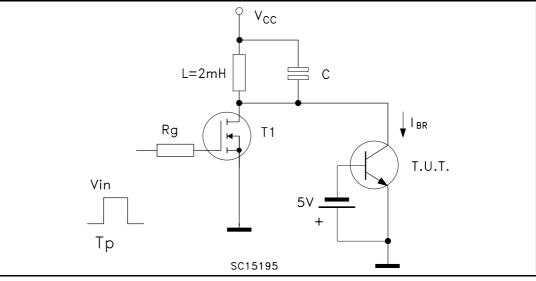
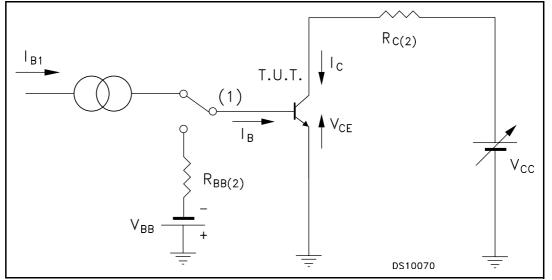


Figure 15. Resistive load switching test circuit





## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM		mm.			inch		
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	МАХ	
А	2.2		2.4	0.086		0.09	
A1	0.9		1.1	0.035		0.04	
A2	0.03		0.23	0.001		0.00	
В	0.64		0.9	0.025		0.03	
b4	5.2		5.4	0.204		0.21	
С	0.45		0.6	0.017		0.02	
C2	0.48		0.6	0.019		0.02	
D	6		6.2	0.236		0.244	
D1		5.1			0.200		
E	6.4		6.6	0.252		0.260	
E1	1	4.7			0.185		
е		2.28			0.090		
e1	4.4		4.6	0.173		0.18	
Н	9.35		10.1	0.368		0.39	
L	1			0.039			
(L1)		2.8			0.110		
L2		0.8			0.031		
L4	0.6		1	0.023		0.039	
R		0.2			0.008		
V2	0°		8°	0°		8°	
	ſ		A		PAD		

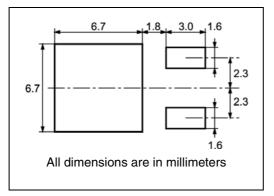
#### **DPAK MECHANICAL DATA**



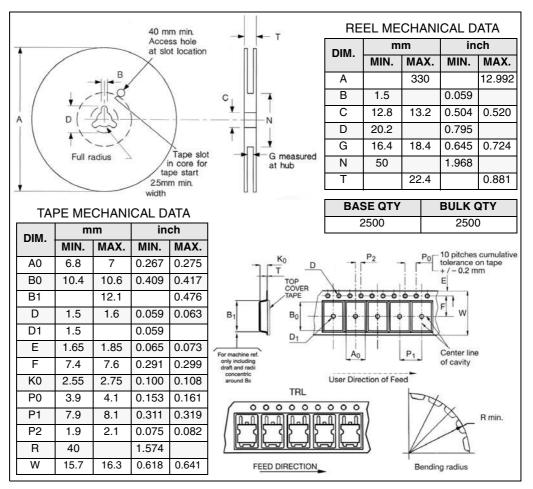
57

## 5 Packaging mechanical data

#### **DPAK FOOTPRINT**



TAPE AND REEL SHIPMENT



## 6 Revision history

#### Table 5.Document revision history

Date	Revision	Changes
09-Aug-2007	1	First release.



#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

